

Product Summary

V _{(BR)DSS}	R _{DS(on)MAX}	I _D
20V	500mΩ@4.5V	0.75A
	700mΩ@2.5V	
	900mΩ@1.8V	

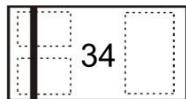
Feature

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low R_{DS(on)}
- Operated at Low Logic Level Gate Drive

Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

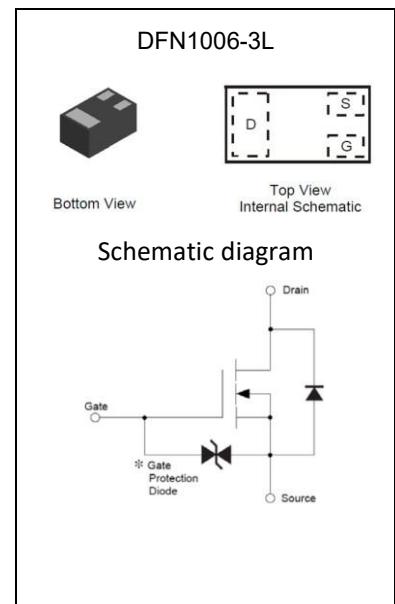
MARKING:



Top View
Bar Denotes Gate
and Source Side

ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Continuous Drain Current ⁽¹⁾	I _D	0.75	A
Pulsed Drain Current(tp=10μs)	I _{DM}	1.8	A
Power Dissipation ⁽¹⁾	P _D	100	mW
Thermal Resistance from Junction to Ambient ⁽¹⁾	R _{θJA}	1250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~+150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	T _L	260	°C





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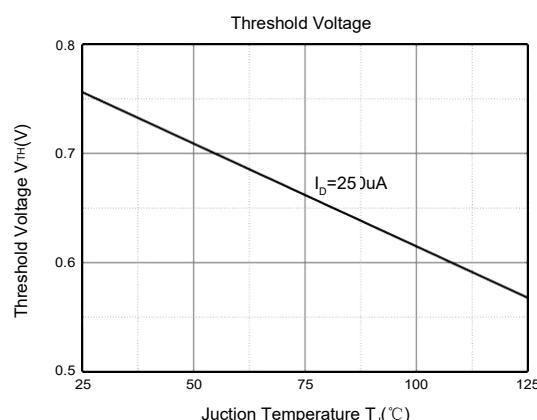
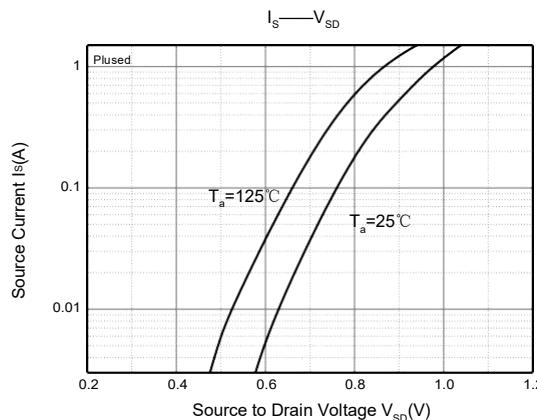
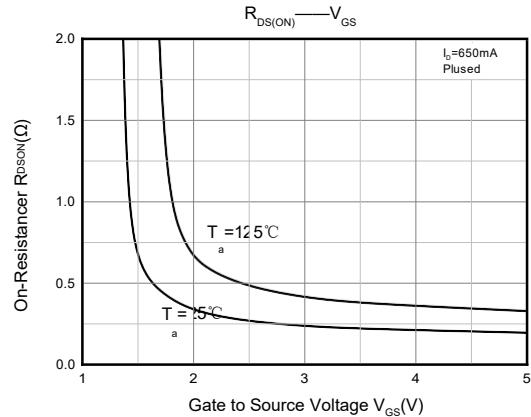
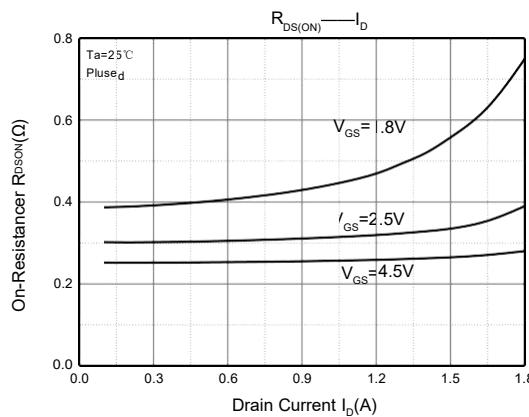
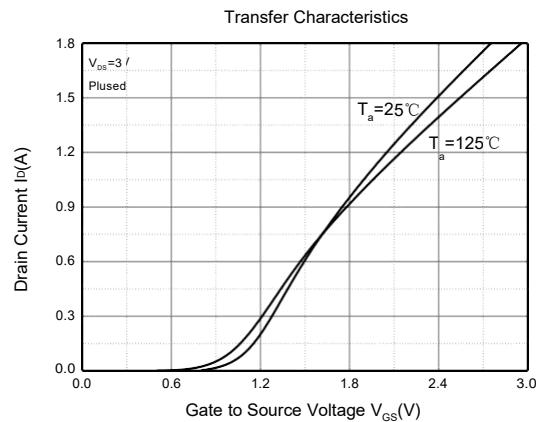
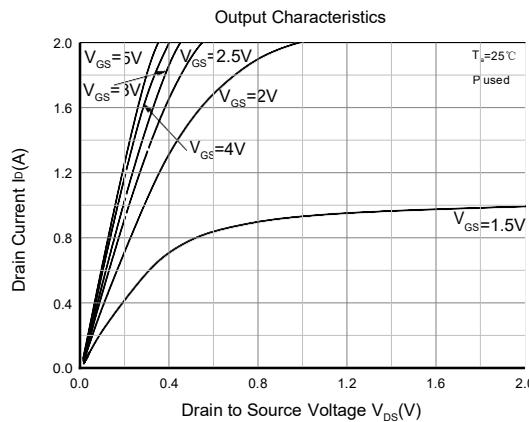
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 20	μA
Gate threshold voltage ⁽²⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.35	0.75	1.1	V
Drain-source on-resistance ⁽²⁾	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 150mA$		250	500	$m\Omega$
		$V_{GS} = 2.5V, I_D = 150mA$		300	700	
		$V_{GS} = 1.8V, I_D = 150mA$		370	900	
		$V_{GS} = 1.5V, I_D = 20mA$		460		
		$V_{GS} = 1.2V, I_D = 10mA$		1200		
Forward transconductance	g_{FS}	$V_{DS} = 10V, I_D = 150mA$	150			mS
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$		79	120	pF
Output Capacitance	C_{oss}			13	20	
Reverse Transfer Capacitance	C_{rss}			9	15	
Switching Characteristics⁽⁴⁾						
Turn-on delay time ⁽³⁾	$t_{d(on)}$	$V_{DS} = 10V, I_D = 500mA, V_{GS} = 4.5V, R_G = 10\Omega$		6.7		ns
Turn-on rise time ⁽³⁾	t_r			4.8		
Turn-off delay time ⁽³⁾	$t_{d(off)}$			17.3		
Turn-off fall time ⁽³⁾	t_f			7.4		
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$I_S = 0.15A, V_{GS} = 0V$			1.2	V

Notes:

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300 μs , Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producing.

Typical Electrical and Thermal Characteristics

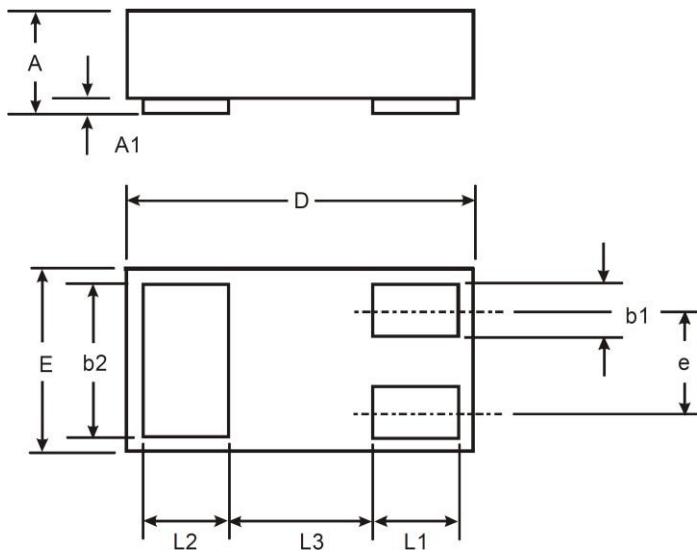




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DFN1006-3L Package Information



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40

All Dimensions in mm

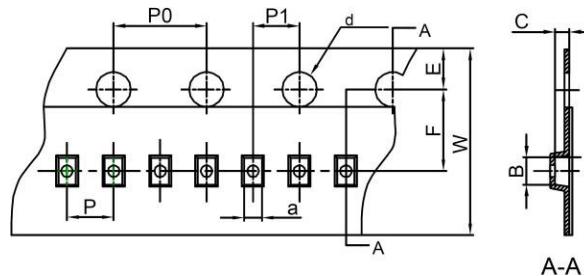


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DFN1006-3L Tape and Ree

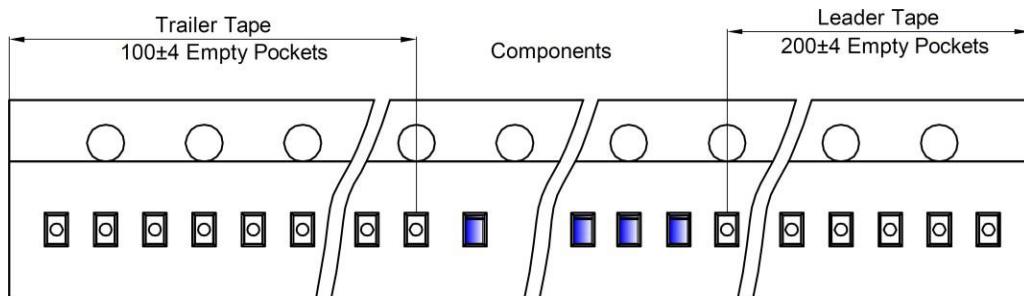
DFN1006-3L Embossed Carrier Tape



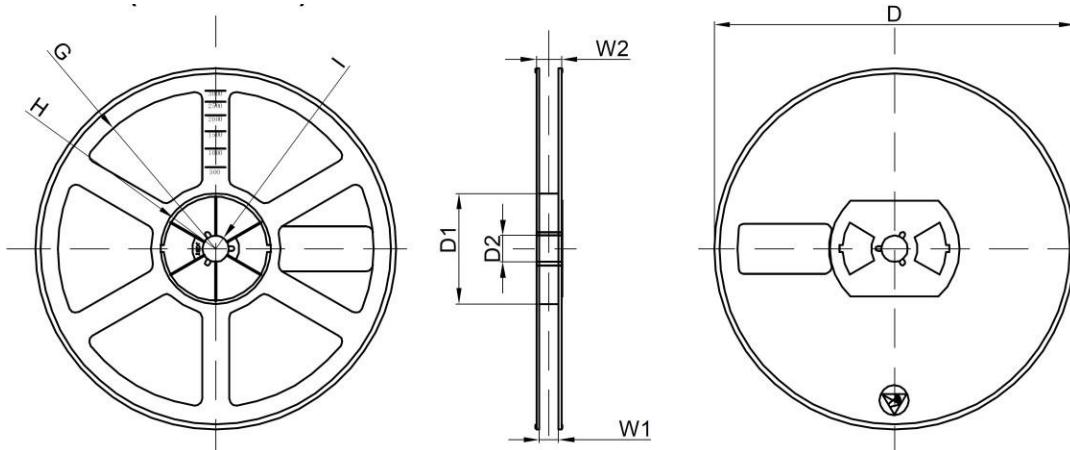
Dimensions are in millimeter

Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFN1006-3L	0.66	1.15	0.66	Ø1.50	1.75	3.50	4.00	2.00	2.00	8.00

DFN1006-3L Tape Leader and Trailer



DFN1006-3L Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
10000 pcs	7 inch	100,000 pcs	203×203×195	400,000 pcs	438×438×220	